

ULP-2 Plastic-Encapsulate Switching Diodes

FSDS160ULP SWITCHING DIODE

DESCRIPTION

Silicon Epitaxial Planar

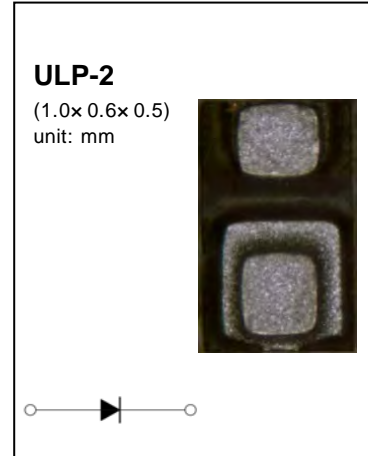
FEATURES

- Small Surface Mounting Type
- High Speed
- High Reliability with High Surge Current Handling Capability

APPLICATION

High Speed Switching for Detection

For Portable Equipment : Mobile Phone,MP3, MD,CD- ROM,DVD- ROM, Note Book PC, etc.



MARKING: 7



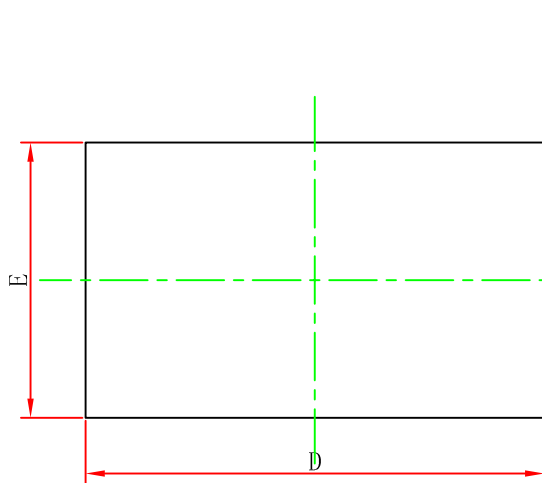
Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Peak Forward Current	I_{FM}	225	mA
Mean Rectifying Current	I_o	100	mA
Surge Current @t=1s	I_{surge}	500	mA
Power dissipation	P_D	100	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	1250	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	- 55~ +150	°C

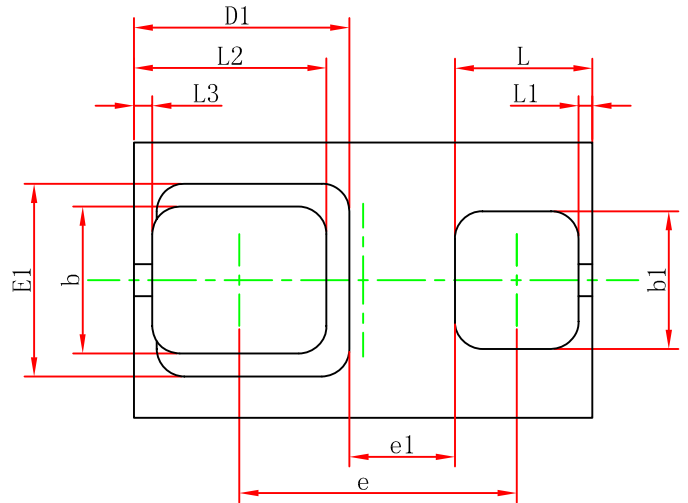
Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_F			1.2	V	$I_F=100mA$
Reverse current	I_R			0.1	μA	$V_R=80V$
Capacitance between terminals	C_T			3.0	pF	$V_R=0.5V, f=1MHz$
Reverse recovery time	t_{rr}			4	ns	$V_R=6V, I_F=10mA, R_L=100\Omega$

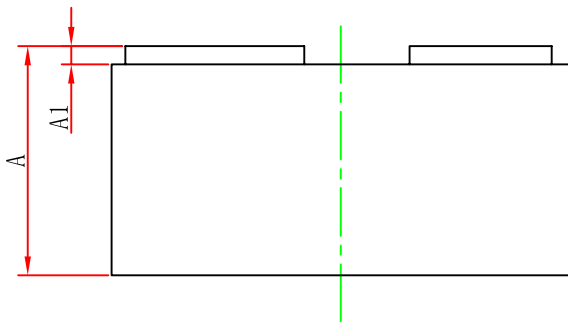
SOD882 / ULP-2



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.100	0.000	0.004
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
D1	0.470REF.		0.019REF.	
E1	0.420REF.		0.017REF.	
b	0.270	0.370	0.011	0.015
b1	0.250	0.350	0.010	0.014
e	0.555	0.655	0.022	0.026
e1	0.230REF.		0.009REF.	
L	0.250	0.350	0.010	0.014
L1	0.030REF.		0.001REF.	
L2	0.370	0.470	0.015	0.019
L3	0.040REF.		0.002REF.	